Silicon Switching Diode

1N4607

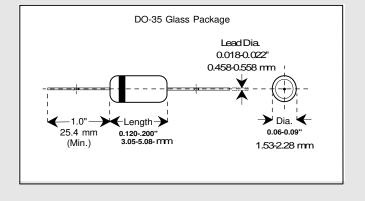
DO-35 Glass Package

Applications

Used in general purpose applications, where a controlled forward characteristic and fast switching speed are important.

Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond[™] plating for problem free solderability



Maximum Ratings			Symbol	Value	Unit
Peak Inverse Voltage			PIV	85 (Min).	Volts
Average Rectified Current			lavg	200	mAmps
Continuous Forward Current			I _{Fdc}	200	mAmps
Peak Surge Current (t _{peak} = 1 sec.)			l peak	1.0	Amp
BKC Power Dissipation $T_{L}=50 \text{ °C}, L = 3/8"$ from body			P _{tot}	500	mWatts
Operating Temperature Range			T _{Op}	-65 to +200	° C
Storage Temperature Range			T _{st}	-65 to +200	° C
Electrical Characteristics @ 25 °C*	Symbol			Maximum	Unit
Forward Voltage Drop @ I _F = 400 mA	$V_{\rm F}$	***		1.10	Volts
Breakdown Voltage @ Ι _R = 25 μA	PIV	85			Volts
Reverse Leakage Current @ $V_{R} = 50 V$	I _R			100	μΑ
Reverse Recovery time (note 1)	t _{rr}			10	nSecs

Note 1: Per Method 4031-A with I_F = 10 mA, Vr = 6 V, R_I = 100 Ohms. * UNLESS OTHERWISE SPECIFIED



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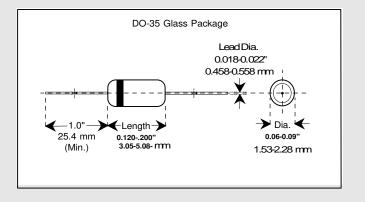
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Features

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Maximum Ratings			Symbo	I Value	Unit
Peak Inverse Voltage			PIV	85 (Min).	Volts
Average Rectified Current			lavg	200	mAmps
Continuous Forward Current			I _{Fdc}	500	mAmps
Peak Surge Current (t _{peak} = 1 sec.)			I _{peak}	1.0	Amp
BKC Power Dissipation $T_L = 50 \text{ °C}, L = 3/8"$ from body			P _{tot}	500	mWatts
Operating Temperature Range			T _{Op}	-65 to +150	° C
Storage Temperature Range			T _{st}	-65 to +150	° C
Electrical Characteristics @ 25 °C*	Symbol	Mi	nimum	Maximum	Unit
Forward Voltage Drop @ $I_F = 400 \text{ mA}$	V_{F}	*	**	1.10	Volts
Breakdown Voltage @ Ι _R = 25 μA	PIV	;	85		Volts
Reverse Leakage Current @ V _R = 50 V	I _R			100	μΑ
Reverse Recovery time (note 1)	t _{rr}			10	nSecs

Note 1: Per Method 4031-A with $I_F = 10 \text{ mA}$, Vr = 6 V, $R_I = 100 \text{ Ohms}$. * UNLESS OTHERWISE SPECIFIED



Silicon Switching Diode



L-35 Glass Package

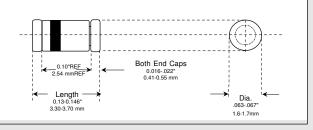
Applications

Used in general purpose applications, where a controlled forward characteristic and fast switching speed are important.

Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond[™] plating for problem free solderability

LL-34/35 MINI MELF Surface Mount Package DO-213AA



Maximum Ratings			Symbol	Value	Unit
Peak Inverse Voltage			PIV	85 (Min).	Volts
Average Rectified Current			lavg	200	mAmps
Continuous Forward Current			I _{Fdc}	200	mAmps
Peak Surge Current (t _{peak} = 1 sec.)			l _{peak}	1.0	Amp
BKC Power Dissipation			P _{tot}	500	mWatts
Operating Temperature Range			Τ _{ορ}	-65 to +200	° C
Storage Temperature Range			T _{st}	-65 to +200	° C
Electrical Characteristics @ 25 °C*	Symbol	Mi	nimum	Maximum	Unit
Forward Voltage Drop @ $I_F = 400 \text{ mA}$	V_{F}	*	***	1.10	Volts
Breakdown Voltage @ Ι _R = 25 μA	PIV	8	85		Volts
Reverse Leakage Current @ V _R = 50 V	l _R			100	μΑ
Reverse Recovery time (note 1)	t _{rr}			10	nSecs

Note 1: Per Method 4031-A with $I_F = 10 \text{ mA}, Vr = 6 \text{ V}, R_L = 100 \text{ Ohms. * UNLESS OTHERWISE SPECIFIED}$



Silicon Switching Diode LL4608

LL-35 Glass Package

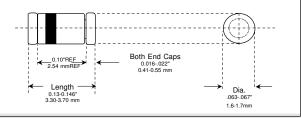
Applications

Used in general purpose applications, where a controlled forward characteristic and fast switching speed are important.

Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability

LL-34/35 MINI MELF Surface Mount Package DO-213AA



Maximum Ratings			Symbol	Value	Unit
Peak Inverse Voltage			PIV	85 (Min).	Volts
Average Rectified Current			lavg	200	mAmps
Continuous Forward Current			I _{Fdc}	500	mAmps
Peak Surge Current (t _{peak} = 1 sec.)			I peak	1.0	Amp
BKC Power Dissipation $T_{L}=50 \text{ °C}, L = 3/8"$ from body			P _{tot}	500	mWatts
Operating Temperature Range			T _{Op}	-65 to +150	° C
Storage Temperature Range			T _{st}	-65 to +150	° C
Electrical Characteristics @ 25 °C*	Symbol	Mi	nimum	Maximum	Unit
Forward Voltage Drop @ I _F = 400 mA	V_{F}	***		1.10	Volts
Breakdown Voltage @ Ι _R =25 μA	PIV	85			Volts
Reverse Leakage Current @ V _R = 50 V	I _R			100	μΑ
Reverse Recovery time (note 1)	t _{rr}			10	nSecs

Note 1: Per Method 4031-A with I_F = 10 mA,Vr = 6 V, R_I = 100 Ohms. * UNLESS OTHERWISE SPECIFIED

